



America Semiconductor

Silicon Fast Recovery Diode

**FR16B02 thru
FR16JR02**

$V_{RRM} = 100\text{ V} - 600\text{ V}$

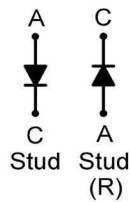
$I_F = 16\text{ A}$

Features

- High Surge Capability
- Types up to 600 V V_{RRM}

Note:

1. Standard polarity: Stud is cathode.
2. Reverse polarity (R): Stud is anode.
3. Stud is base.



DO-4 Package



Maximum ratings, at $T_j = 25\text{ °C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	FR16B(R)02	FR16D(R)02	FR16G(R)02	FR16J(R)02	Unit
Repetitive peak reverse voltage	V_{RRM}		100	200	400	600	V
RMS reverse voltage	V_{RMS}		70	140	280	420	V
DC blocking voltage	V_{DC}		100	200	400	600	V
Continuous forward current	I_F	$T_C \leq 100\text{ °C}$	16	16	16	16	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$, $t_p = 8.3\text{ ms}$	225	225	225	225	A
Operating temperature	T_j		-65 to 150	-65 to 150	-65 to 150	-65 to 150	°C
Storage temperature	T_{stg}		-65 to 175	-65 to 175	-65 to 175	-65 to 175	°C

Electrical characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	FR16B(R)02	FR16D(R)02	FR16G(R)02	FR16J(R)02	Unit
Diode forward voltage	V _F	I _F = 16 A, T _j = 25 °C	1.4	1.4	1.4	1.4	V
Reverse current	I _R	V _R = 100 V, T _j = 25 °C	25	25	25	25	μA
		V _R = 100 V, T _j = 150 °C	6	6	6	6	mA
Recovery Time							
Maximum reverse recovery time	T _{RR}	I _F =0.5 A, I _R =1.0 A, I _{RR} = 0.25 A	200	200	200	250	nS
Thermal characteristics							
Thermal resistance, junction - case	R _{thJC}		1.5	1.5	1.5	1.5	°C/W



